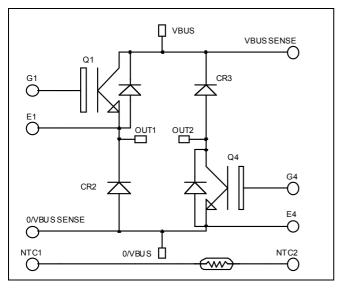


Asymmetrical - Bridge Trench + Field Stop IGBT3 Power Module



O/VBUS

O/VBUS

 $V_{CES} = 600V$ $I_C = 100A$ @ Tc = 80°C

Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Trench + Field Stop IGBT3 Technology
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
 - Symmetrical design
 - Lead frames for power connections
- Internal thermistor for temperature monitoring
- High level of integration



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OUT2

OUT1

NTC2

NTC1 (

- Stable temperature behavior
- Very rugged
- Solderable terminals for easy PCB mounting
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive T_C of V_{CEsat}
- Low profile
- **RoHS Compliant**

Absolute maximum ratings

Ø VBUS

SENSE

0 E1

Symbol	Parameter		Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage		600	V
I_{C}	Continuous Collector Current	$T_C = 25^{\circ}C$	150	
1 _C	Continuous Conector Current	$T_C = 80^{\circ}C$	100	A
I_{CM}	Pulsed Collector Current	$T_C = 25$ °C	200	
V_{GE}	Gate – Emitter Voltage		±20	V
P_{D}	Maximum Power Dissipation	$T_C = 25$ °C	340	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 150^{\circ}C$	200A @ 550V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note

APTGT100DH60TG-Rev 2 October, 2012



All ratings @ $T_j = 25$ °C unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 600V$				250	μΑ
V	Collector Emitter Saturation Voltage	$V_{GE} = 15V$	$T_j = 25$ °C		1.5	1.9	V
V _{CE(sat)}	Confector Emitter Saturation Voltage	$I_{\rm C} = 100A$	$T_j = 150$ °C		1.7		ı v
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 1.5 \text{ mA}$		5.0	5.8	6.5	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V$, $V_{CE} = 0V$				400	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$		6100		
C_{oes}	Output Capacitance	$V_{CE} = 25V$		390		pF
C_{res}	Reverse Transfer Capacitance	f = 1MHz		190		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C)		115		
T_{r}	Rise Time	$V_{GE} = \pm 15V$		45		
$T_{d(off)}$	Turn-off Delay Time	$V_{\text{Bus}} = 300V$ $I_{\text{C}} = 100A$		225		ns
T_{f}	Fall Time	$R_G = 3.3\Omega$		55		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (150°C)		130		
T_{r}	Rise Time	$V_{GE} = \pm 15V$		50		
$T_{d(off)}$	Turn-off Delay Time	$V_{\text{Bus}} = 300V$ $I_{\text{C}} = 100A$		300		ns
$T_{\rm f}$	Fall Time	$R_G = 3.3\Omega$		70		
Б	Turn on Energy	$V_{GE} = \pm 15V$ $T_j = 25^{\circ}C$		0.4		ma I
Eon	Turn on Energy	$V_{\text{Bus}} = 300\text{V}$ $T_{\text{j}} = 150^{\circ}\text{C}$		0.875		mJ
E	Turn off Engrav	$I_C = 100A$ $T_j = 25^{\circ}C$		2.5		ma I
E_{off}	Turn off Energy	$R_G = 3.3\Omega$ $T_j = 150$ °C		3.5		mJ

Diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Test Conditions		Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			600			V
I_{RM}	Maximum Reverse Leakage Current	V _R =600V	$T_i = 25^{\circ}C$ $T_i = 150^{\circ}C$			250 500	μА
I_{F}	DC Forward Current		$Tc = 80^{\circ}C$		100	300	A
$V_{\rm F}$	Diode Forward Voltage	$I_F = 100A$ $V_{GE} = 0V$	$T_i = 25^{\circ}C$		1.6	2	V
V _F	Diode Forward Voltage		$T_{i} = 150^{\circ}C$		1.5		v
t_{rr}	Reverse Recovery Time	$I_F = 100A$ $V_R = 300V$ $T_j = T_j = T_$	$T_j = 25$ °C		125		ns
ιr			$T_{j} = 150^{\circ}C$		220		
0	1 · 1 := /.) (,		$T_j = 25$ °C		4.7		μС
Q_{rr}				9.9		μС	
E _r	Reverse Recovery Energy		$T_j = 25$ °C		1.1		mJ
$\mathbf{E}_{\mathbf{r}}$			$T_{\rm j} = 150^{\circ}{\rm C}$		2.4		1113

APTGT100DH60TG - Rev 2 October, 2012

2 - 6



Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

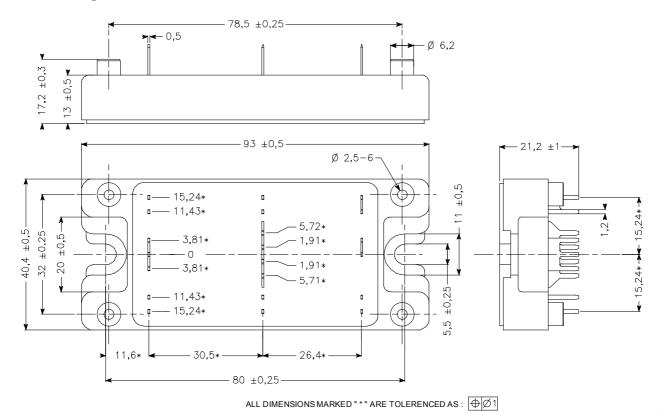
Symbol	Characteristic	Min	Тур	Max	Unit	
R ₂₅	Resistance @ 25°C		50		kΩ	
${ m B}_{25/85}$	$T_{25} = 298.15 \text{ K}$		3952		K	

$$R_T = \frac{R_{25}}{\exp \left[B_{25/85} \left(\frac{1}{T_{25}} - \frac{1}{T} \right) \right]}$$
 T: Thermistor temperature R_T: Thermistor value at T

Thermal and package characteristics

Symbol	Characteristic			Min	Тур	Max	Unit
R_{thJC}	Junction to Case Thermal Resistance		IGBT			0.44	°C/W
KthJC	Junction to Case Thermal Resistance		Diode			0.77	C/ W
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
T_{J}	Operating junction temperature range		-40		175		
T_{STG}	Storage Temperature Range		-40		125	°C	
$T_{\rm C}$	Operating Case Temperature		-40		100		
Torque	Mounting torque	To Heatsink	M5	2.5		4.7	N.m
Wt	Package Weight					160	g

SP4 Package outline (dimensions in mm)

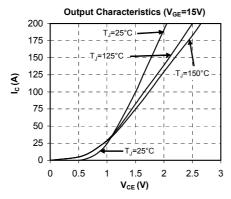


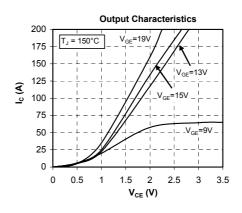
See application note APT0501 - Mounting Instructions for SP4 Power Modules on www.microsemi.com

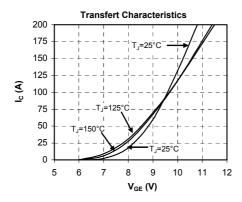
APTGT100DH60TG-Rev 2 October, 2012

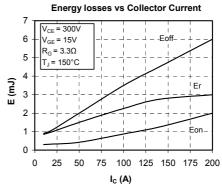


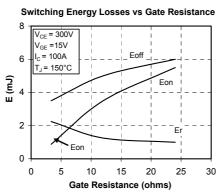
Typical Performance Curve

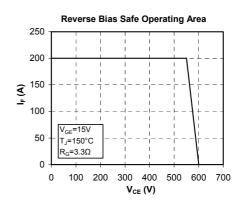


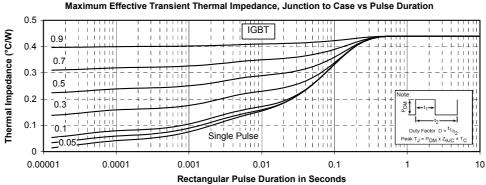






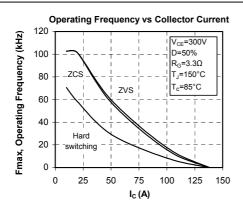


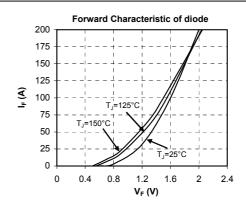


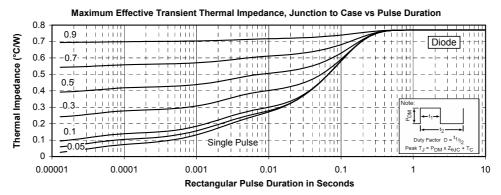


APTGT100DH60TG - Rev 2 October, 2012









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5 - 6



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APTGT100DH60TG - Rev 2 October, 2012